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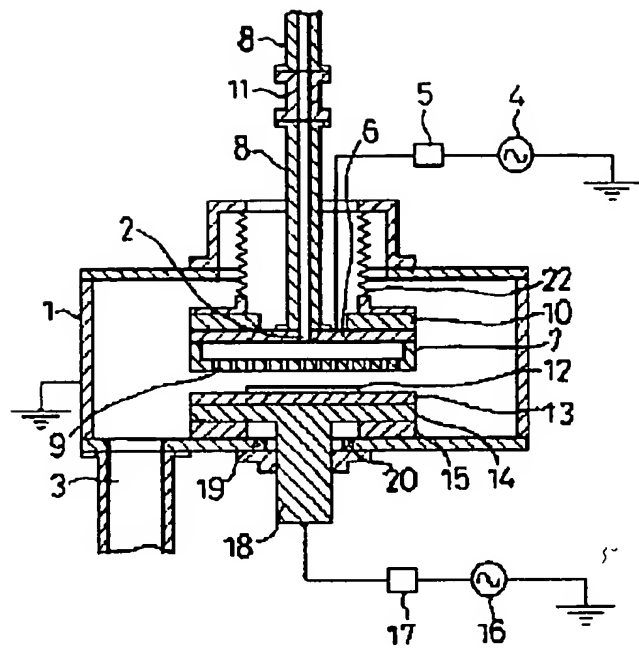
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TITLE : PLASMA CVD DEVICE AND METHOD



ABSTRACT : PURPOSE: To enable the flat film in high stepped part covering coefficient to be deposition-formed by a method wherein the title plasma CVD device is provided with a means for feeding a substrate mounting base with a specific low-frequency power, another means for feeding a plasma discharging electrode oppositely oriented in the substrate mounting base with a high-frequency power and a bellows freely lifting the plasma discharging electrode.

CONSTITUTION: The title plasam CVD device is provided with a low-frequency oscillator 16 feeding a substrate mounting base 13 with low-frequency power of 200KHz-1MHz, a high-frequency oscillator 4 feeding a plasma discharging electrode 7 oppositely arranged on the substrate mounting base 13 with high-frequency power as well as an elastic cylidrical bellows 22 supporting the plasma discharging electrode 7 in free-lifting mode and adjusting the interval between the substrate mounting base 13 and the plasma discharging electrode 7. Furthermore, said interval and the pressure in a reaction chamber are adjusted so that the stage of feeding both high and low frequency powers and the stage of feeding the low-frequency power only may be combined with each other to deposit flat films on a substrate.

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